

2823



PTO/SB/21 (08-00)

# TRANSMITTAL FORM

(to be used for all correspondence after initial filing)

<b>TRANSMITTAL FORM</b>	Application Number	09/894,125
	Filing Date	June 29, 2001
	First Named Inventor	Shunpei YAMAZAKI et al.
	Group Art Unit	.2823
	Examiner Name	B. Kebede
Total Number of Pages in This Submission	Attorney Docket Number	0756-2330

## ENCLOSURES (check all that apply)

<input type="checkbox"/> Fee Transmittal Form <input type="checkbox"/> Fee Attached <input checked="" type="checkbox"/> Amendment / Reply <input type="checkbox"/> After Final <input type="checkbox"/> Affidavits/declaration(s) <input type="checkbox"/> Extension of Time Request <input type="checkbox"/> Express Abandonment Request <input type="checkbox"/> Information Disclosure Statement <input type="checkbox"/> Certified Copy of Priority Document(s) <input type="checkbox"/> Response to Missing Parts/Incomplete Application <input type="checkbox"/> Response to Missing Parts under 37 CFR 1.52 or 1.53	<input type="checkbox"/> Assignment Papers (for an Application) <input type="checkbox"/> Drawing(s) <input type="checkbox"/> Declaration and Power of Attorney <input type="checkbox"/> Licensing-related Papers <input type="checkbox"/> Petition <input type="checkbox"/> Petition to Convert to a Provisional Application <input type="checkbox"/> Power of Attorney, Revocation Change of Correspondence Address <input type="checkbox"/> Terminal Disclaimer <input type="checkbox"/> Request for Refund <input type="checkbox"/> CD, Number of CD(s) _____	<input type="checkbox"/> After Allowance Communication to Group <input type="checkbox"/> Appeal Communication to Board of Appeals and Interferences <input type="checkbox"/> Appeal Communication to Group (Appeal Notice, Brief, Reply Brief) <input type="checkbox"/> Proprietary Information <input type="checkbox"/> Status Letter <input type="checkbox"/> Other Enclosures 1. 2. 3. 4. 5. 6.
Remarks <input checked="" type="checkbox"/> The Commissioner is hereby authorized to charge any additional fees required or credit any overpayments to Deposit Account No. 50-2280 for the above identified docket number.		

## SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT

Firm or Individual name	Eric J. Robinson, Reg. No. 38,285 Robinson Intellectual Property Law Office, P.C. PMB 955 21010 Southbank Street Potomac Falls, VA 20165
Signature	
Date	2-20-03

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Patent Application of )

Art Unit: 2823

Shunpei YAMAZAKI et al. )

Examiner: B. Kebede

Serial No. 09/894,125 ✓ )

Filed: June 29, 2001 ✓ )

For: CRYSTALLINE SEMICONDUCTOR) )

THIN FILM, METHOD OF FABRICATING )

THE SAME, SEMICONDUCTOR DEVICE,) )

AND METHOD OF FABRICATING THE )

SAME )

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Adele M. Stamper

AMENDMENT

Honorable Commissioner of Patents

Washington, D.C. 20231

Sir:

In response to the Official Action dated November 20, 2002, please amend the  
above-identified application as follows:

IN THE CLAIMS:

Please amend claims 1 and 7 as follows:

1. (Twice Amended) A method of manufacturing a semiconductor device  
comprising the steps of:

forming a semiconductor film comprising silicon over a substrate;

irradiating said semiconductor film with laser light in air for crystallizing  
said semiconductor film;

removing a natural oxidation film formed on a surface of the  
semiconductor film by etching after the irradiation of the laser light; and

leveling the surface of the semiconductor film by heating after removing  
said natural oxidation film.

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